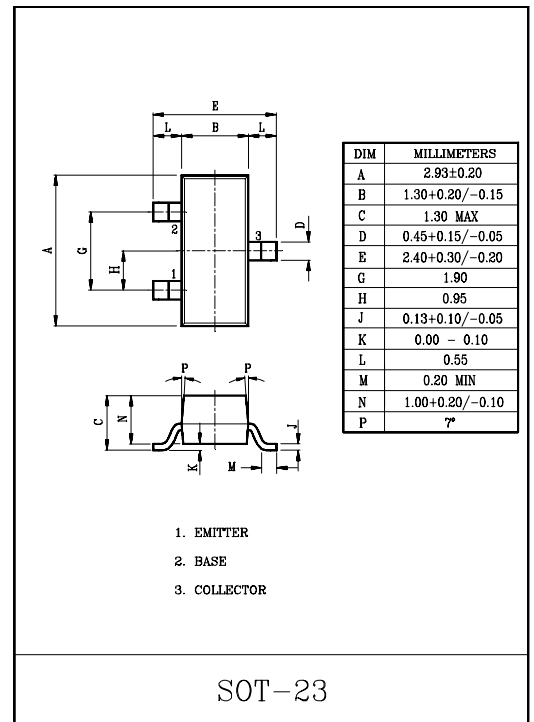
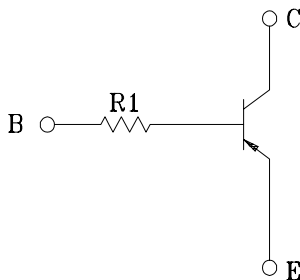


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

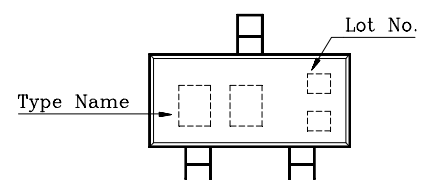
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I _{CBO}	V _{CB} =-50V, I _E =0	-	-	-100	nA
Emitter Cut-off Current		I _{EBO}	V _{EB} =-5V, I _C =0	-	-	-100	nA
DC Current Gain		h _{FE}	V _{CE} =-5V, I _C =-1mA	120	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA	-	-0.1	-0.3	V
Transition Frequency		f _T *	V _{CE} =-10V, I _C =-5mA	-	250	-	MHz
Input Resistor	KRA110S	R _I		-	4.7	-	k Ω
	KRA111S			-	10	-	
	KRA112S			-	100	-	
	KRA113S			-	22	-	
	KRA114S			-	47	-	

Note : *Characteristic of Transistor Only

MARK SPEC

TYPE	KRA110S	KRA111S	KRA112S	KRA113S	KRA114S
MARK	PK	PM	PN	PO	PP

Marking



KRA110S ~ KRA114S

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC			SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Switching Time	Rise Time	KRA110S	t _r	V _O =-5V V _{IN} =-5V R _L =1kΩ	-	0.2	-	μS
		KRA111S			-	0.065	-	
		KRA112S			-	0.4	-	
		KRA113S			-	0.1	-	
		KRA114S			-	0.15		
	Storage Time	KRA110S	t _{stg}		-	2.0	-	
		KRA111S			-	1.7	-	
		KRA112S			-	3.0	-	
		KRA113S			-	2.0	-	
		KRA114S			-	1.5	-	
	Fall Time	KRA110S	t _f		-	0.3	-	
		KRA111S			-	0.3	-	
		KRA112S			-	1.7	-	
		KRA113S			-	0.8	-	
		KRA114S			-	1.5	-	